



MMBT3904B

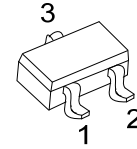
Preliminary

NPN EPITAXIAL SILICON TRANSISTOR

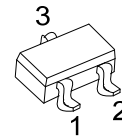
GENERAL PURPOSE APPLICATION

■ FEATURES

- * Collector-Emitter Voltage: $V_{CE0}=40V$
- * Complementary to UTC MMBT3906B



SOT-23
(JEDEC TO-236)



SOT-523

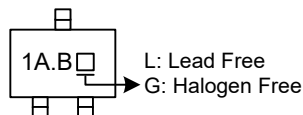
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
MMBT3904BL-AE3-R	MMBT3904BG-AE3-R	SOT-23	B	E	C	Tape Reel
MMBT3904BL-AN3-R	MMBT3904BG-AN3-R	SOT-523	B	E	C	Tape Reel

Note: Pin Assignment: B: Base E: Emitter C: Collector

MMBT3904BG-AE3-R (1) Packing Type (2) Package Type (3) Green Package	(1) R: Tape Reel (2) AE3: SOT-23, AN3: SOT-523 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATING** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	60	V
Collector-Emitter Voltage		V_{CEO}	40	V
Emitter-Base Voltage		V_{EBO}	6	V
Collector Current		I_C	200	mA
Collector Dissipation	SOT-23	P_C	0.35	W
	SOT-523		0.27	W
Junction Temperature		T_J	+150	$^{\circ}\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.
Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ **THERMAL CHARACTERISTICS**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	SOT-23	θ_{JA}	360	$^{\circ}\text{C/W}$
	SOT-523		450	$^{\circ}\text{C/W}$

Note: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

■ **ELECTRICAL CHARACTERISTICS** ($T_A=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	V_{CBO}	$I_C=10\mu\text{A}$, $I_E=0$	60			V
Collector-Emitter Breakdown Voltage	V_{CEO}	$I_C=1\text{mA}$, $I_B=0$ (Note)	40			V
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E=10\mu\text{A}$, $I_C=0$	6			V
Collector-Emitter Saturation Voltage (Note)	$V_{CE(SAT)1}$	$I_C=10\text{mA}$, $I_B=1\text{mA}$			0.2	V
	$V_{CE(SAT)2}$	$I_C=50\text{mA}$, $I_B=5\text{mA}$			0.3	V
Base-Emitter Saturation Voltage (Note)	$V_{BE(SAT)1}$	$I_C=10\text{mA}$, $I_B=1\text{mA}$	0.65		0.85	V
	$V_{BE(SAT)2}$	$I_C=50\text{mA}$, $I_B=5\text{mA}$			0.95	V
Collector Cut-Off Current	I_{CEX}	$V_{CE}=30\text{V}$, $V_{EB}=3\text{V}$			50	nA
Base Cut-Off Current	I_{BL}	$V_{CE}=30\text{V}$, $V_{EB}=3\text{V}$			50	nA
DC Current Gain (Note)	h_{FE1}	$V_{CE}=1\text{V}$, $I_C=0.1\text{mA}$	40			
	h_{FE2}	$V_{CE}=1\text{V}$, $I_C=1\text{mA}$	70			
	h_{FE3}	$V_{CE}=1\text{V}$, $I_C=10\text{mA}$	100		300	
	h_{FE4}	$V_{CE}=1\text{V}$, $I_C=50\text{mA}$	60			
	h_{FE5}	$V_{CE}=1\text{V}$, $I_C=100\text{mA}$	30			
Current Gain Bandwidth Product	f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	300			MHz
Output Capacitance	C_{OB}	$V_{CB}=5\text{V}$, $I_E=0$, $f=1\text{MHz}$			4	pF
Turn On Time	t_{ON}	$V_{CC}=3\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$			70	ns
Turn Off Time	t_{OFF}	$I_{B1}=I_{B2}=1\text{mA}$			250	ns

Note: Pulse test: $P_W \leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.

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